

SiC Diode Power Module



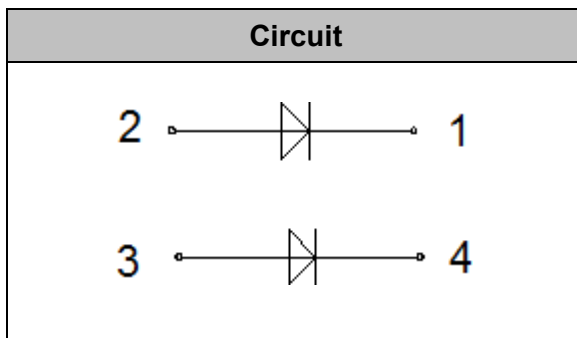
V_{DC}	1200V
I_F	2×100A
$T_{J,max}$	175°C

Applications

- Welding equipment
- Uninterruptible power supply (UPS)
- High frequency power supply
- Induction heating
- High speed rectifiers

Features

- SiC Schottky Diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature independent switching behavior
 - Positive temperature coefficient on V_F
- Very low stray inductance
- Low forward voltage
- Isolated package (SOT-227)
- Low noise switching
- RoHS compliant



■ Absolute Maximum Ratings ($T_J=25^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	VALUE	UNIT
Peak Repetitive Reverse Voltage	V_{RRM}	$T_J=25^\circ\text{C}$	1200	V
DC Blocking Voltage	V_{DC}	$T_J=25^\circ\text{C}$	1200	V
Continuous Forward Current	I_F	$T_C=25^\circ\text{C}, T_J=175^\circ\text{C}$	131	A
		$T_C=96^\circ\text{C}, T_J=175^\circ\text{C}$	100	
		$T_C=135^\circ\text{C}, T_J=175^\circ\text{C}$	56	
Non-Repetitive Peak Forward Surge Current	I_{FSM}	$T_C=25^\circ\text{C}, T_P=10\text{ms}, \text{Half Sine Wave}$	495	A
I^2t Value	$\int I^2 dt$	$T_C=25^\circ\text{C}, T_P=10\text{ms}$	1225	A^2s
Power Dissipation	P_{Tot}	$T_C=25^\circ\text{C}$	375	W
Operating Junction Temperature	$T_{J,op}$		-40...175	$^\circ\text{C}$
Storage Temperature	T_{STG}		-40...125	$^\circ\text{C}$



MB200DU12FJ

■ Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	VALUE			UNIT
			Min.	Typ.	Max.	
Reverse Current	I_R	$V_R=1200\text{V}$, $T_J=25^{\circ}\text{C}$	--	6	100	μA
		$V_R=1200\text{V}$, $T_J=175^{\circ}\text{C}$	--	21.5	--	
Forward Voltage	V_F	$I_F=100\text{A}$, $T_J=25^{\circ}\text{C}$	--	1.45	1.7	V
		$I_F=100\text{A}$, $T_J=175^{\circ}\text{C}$	--	1.97	--	
Total Capacitance	C	$V_R=1\text{V}$, $f=1\text{MHz}$	--	5517	--	pF
		$V_R=400\text{V}$, $f=1\text{MHz}$	--	478	--	
		$V_R=800\text{V}$, $f=1\text{MHz}$	--	357	--	
Total Capacitive Charge	Q_C	$V_R=800\text{V}$	--	509	--	nC
Capacitance Stored Energy	E_C	$V_R=800\text{V}$	--	132	--	μJ

■ Thermal and Package Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	VALUE			UNIT
			Min.	Typ.	Max.	
Thermal Resistance, Junction to Case	R_{thJC}	Per leg		0.40		$^{\circ}\text{C/W}$
Isolation Breakdown Voltage	V_{isol}	AC, 50Hz (R.M.S), $t=1\text{min}$	3000			V
Mounting Torque	M	Recommended (M4 screw)	0.6		1.2	Nm
Terminal Connection Torque		Recommended (M4 screw)	0.6		1	
Weight	W			27		g



■ Typical Performance Per Leg

Fig1. Forward Characteristics

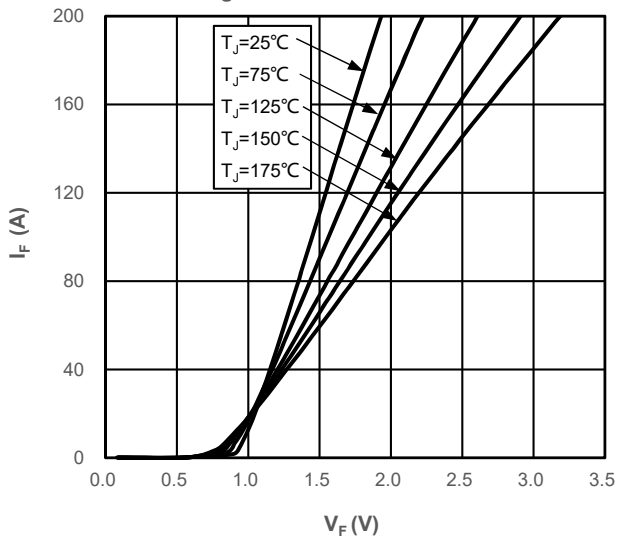


Fig2. Reverse Characteristics

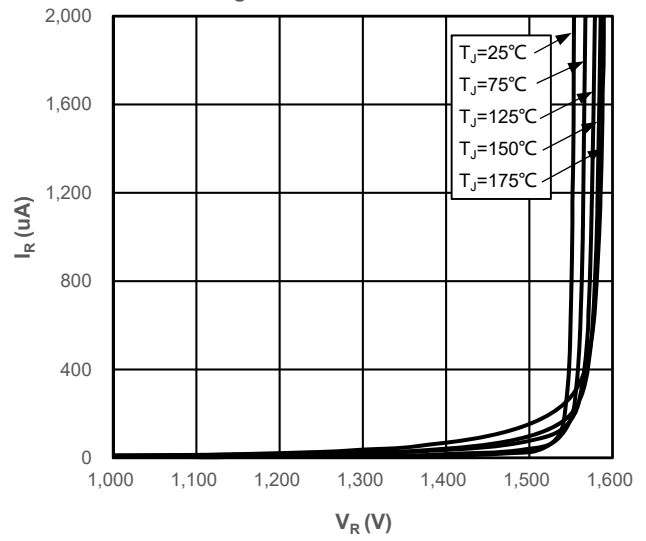


Fig3. Current Derating

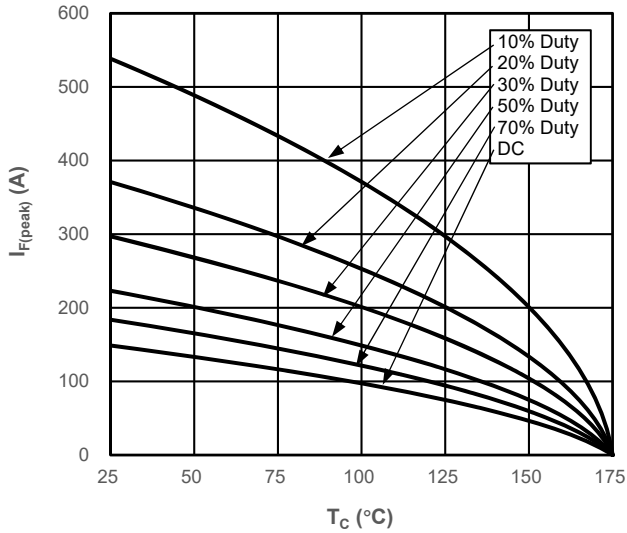


Fig4. Power Derating

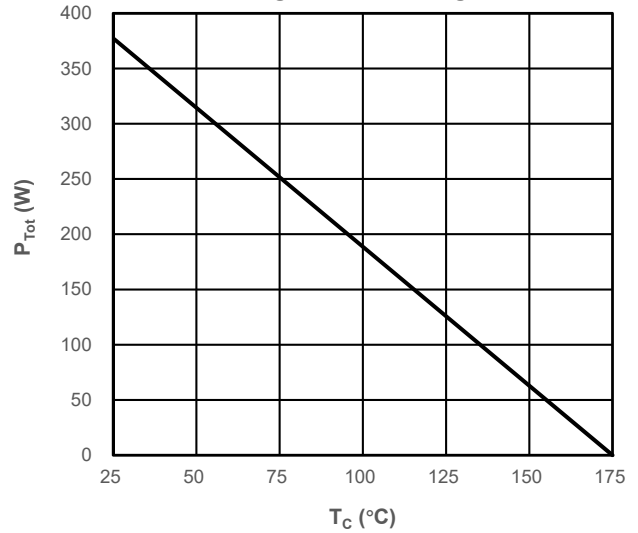


Fig5. Recovery Charge vs. Reverse Voltage

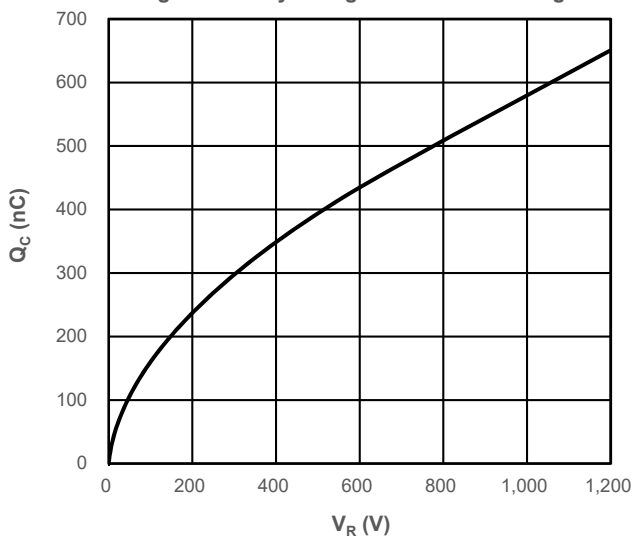


Fig6. Capacitance vs. Reverse Voltage

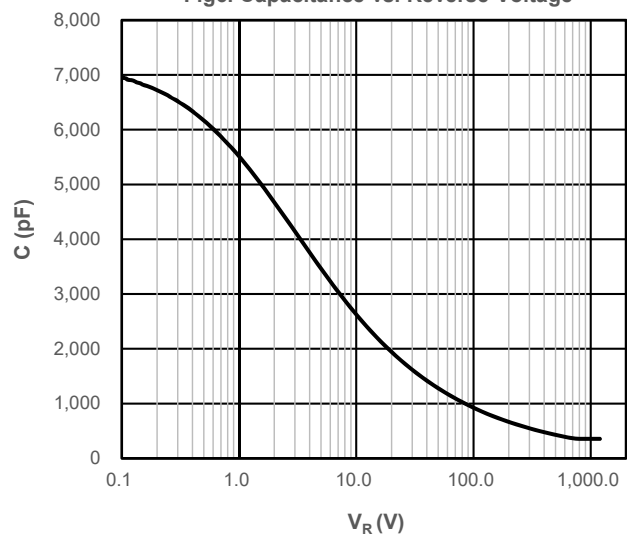




Fig7. Typical Capacitance Stored Energy

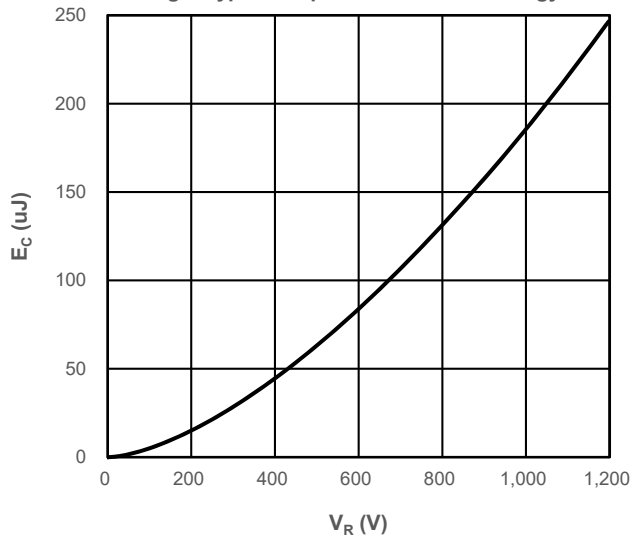
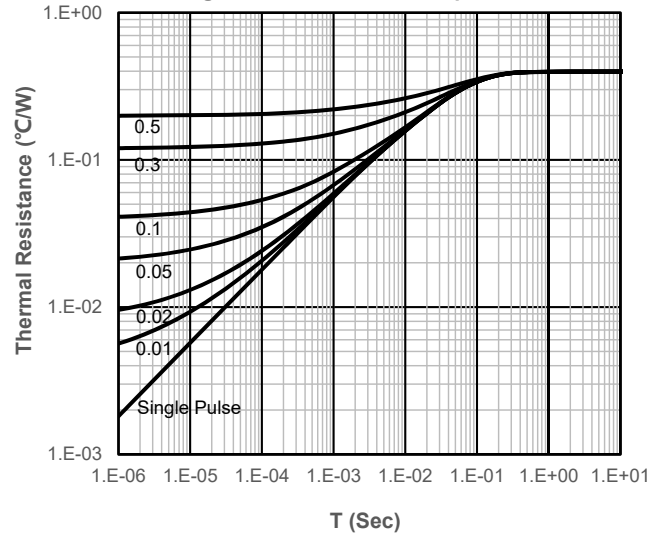


Fig8. Transient Thermal Impedance





Dimensions in mm



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